

HSC2412

General Purpose Transistors NPN Silicon

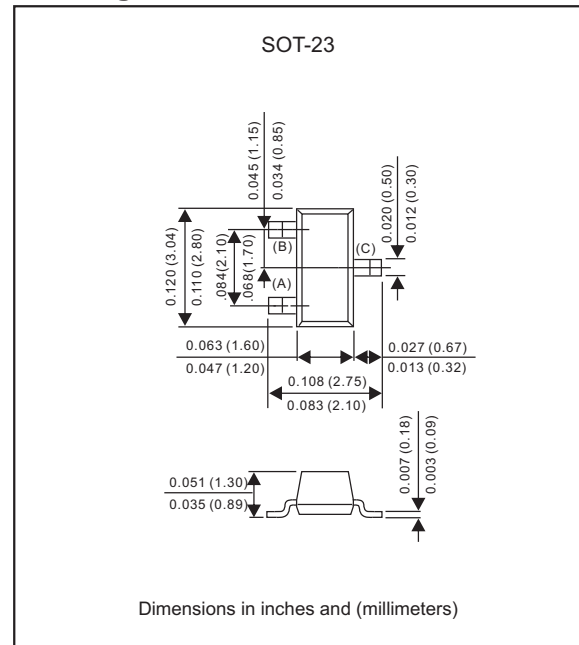
Features

- We declare that the material of product compliance with RoHS requirements
- Lead-free parts for green partner, exceeds environmental standards of MIL-STD-19500 /228

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-23
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any
- Weight : Approximated 0.008 gram

Package outline



Maximum ratings (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

| Rating | Symbol | Value | Unit |
|--------------------------------------|-----------|----------|--------------------|
| Collector–Emitter Voltage | V_{CE0} | 50 | V |
| Collector–Base Voltage | V_{CBO} | 60 | V |
| Emitter–Base Voltage | V_{EBO} | 7.0 | V |
| Collector Current — Continuous | I_C | 150 | mAdc |
| Collector power dissipation | P_D | 0.2 | W |
| Operating junction temperature range | T_J | -55~+150 | $^{\circ}\text{C}$ |
| Storage temperature range | T_{STG} | -55~+150 | $^{\circ}\text{C}$ |

Electrical characteristics (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

| Characteristic | Conditions | Symbol | Min. | Typ. | Max. | Unit |
|--------------------------------------|--|---------------|------|------|------|---------------|
| Collector–Emitter Breakdown Voltage | $I_C=1\text{mA}$ | $V_{(BR)CE0}$ | 50 | | | V |
| Emitter–Base Breakdown Voltage | $I_E=50\mu\text{A}$ | $V_{(BR)EBO}$ | 7 | | | V |
| Collector–Base Breakdown Voltage | $I_C=50\mu\text{A}$ | $V_{(BR)CBO}$ | 60 | | | V |
| Collector Cutoff Current | $V_{CB}=60\text{V}$ | I_{CBO} | | | 0.1 | μA |
| Emitter cutoff current | $V_{EB}=7\text{V}$ | I_{EBO} | | | 0.1 | μA |
| Collector-emitter saturation voltage | $I_C / I_E=50\text{mA} / 5\text{mA}$ | $V_{CE(sat)}$ | | | 0.4 | V |
| DC current transfer ratio | $V_{CE}=6\text{V}, I_C=1\text{mA}$ | h_{FE} | 120 | | 560 | - |
| Transition frequency | $V_{CE}=12\text{V}, I_E=-2\text{mA}, f=30\text{MHz}$ | f_T | | 180 | | MHZ |
| Output capacitance | $V_{CB}=12\text{V}, I_E=0\text{A}, f=1\text{MHz}$ | C_{ob} | | 2.0 | 3.5 | pF |

h_{FE} values are classified as follows:

| * | Q | R | S |
|----------|---------|---------|---------|
| h_{FE} | 120~270 | 180~390 | 270~560 |

Rating and characteristic curves (HSC2412)

Fig.1 Grounded emitter propagation characteristics

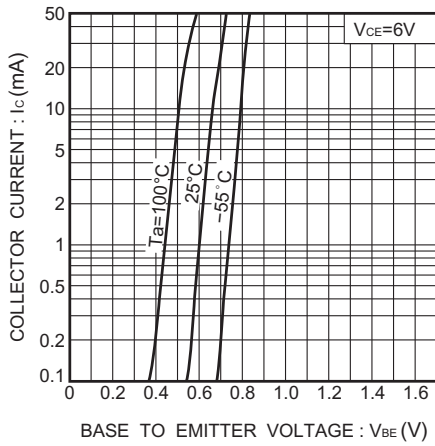


Fig.2 Grounded emitter output characteristics (I)

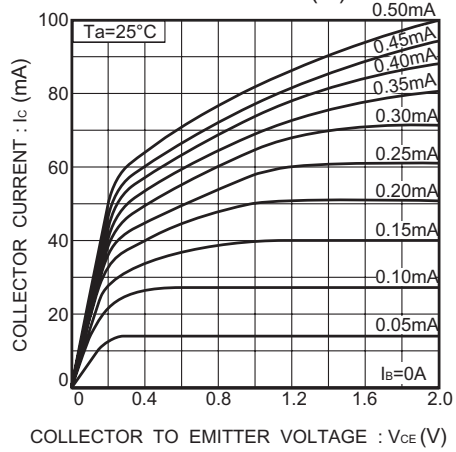


Fig.3 Grounded emitter output characteristics (II)

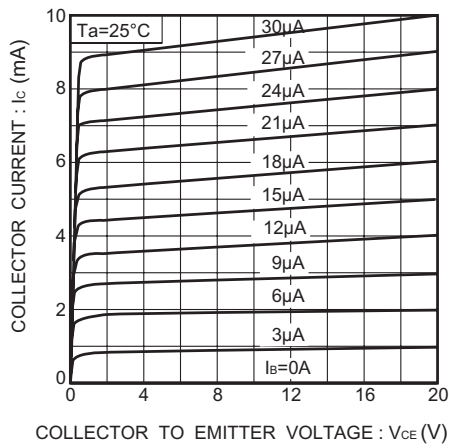


Fig.4 DC current gain vs. collector current (I)

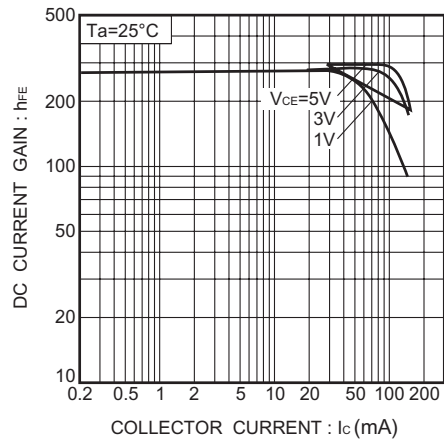


Fig.5 DC current gain vs. collector current (II)

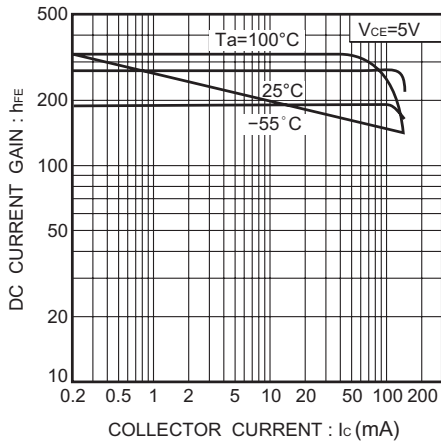
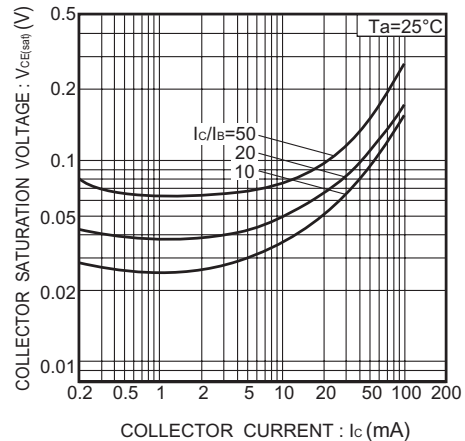


Fig. 6 Collector-emitter saturation voltage vs. collector current



Rating and characteristic curves (HSC2412)

Fig.7 Collector-emitter saturation voltage vs. collector current (I)

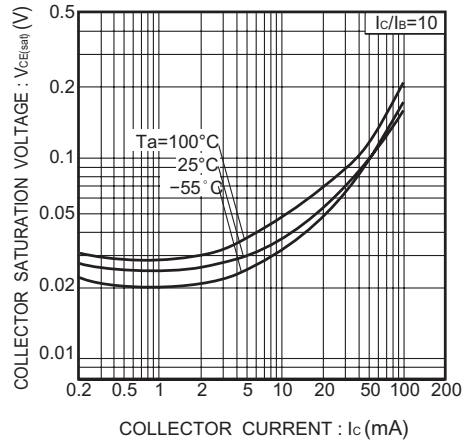


Fig.8 Collector-emitter saturation voltage vs. collector current (II)

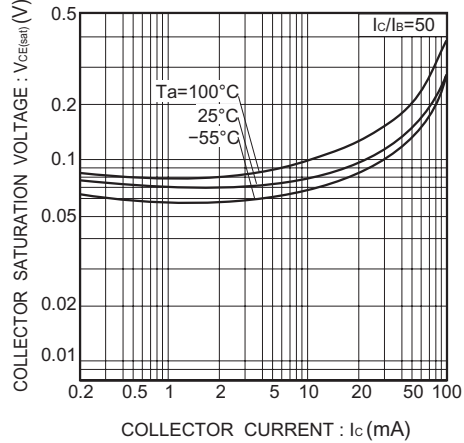


Fig.9 Gain bandwidth product vs. emitter current

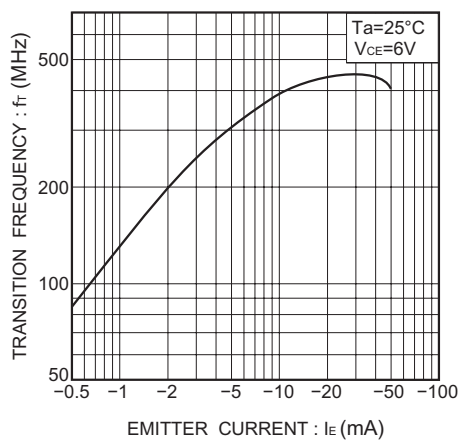


Fig.10 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

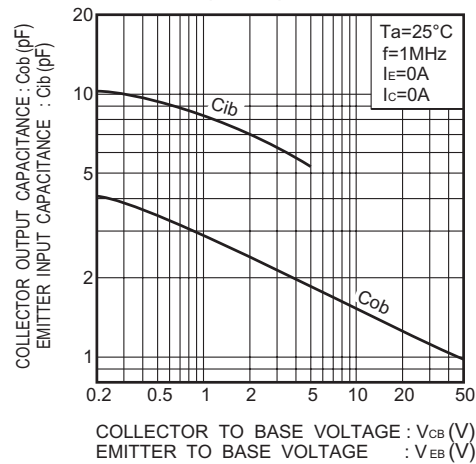
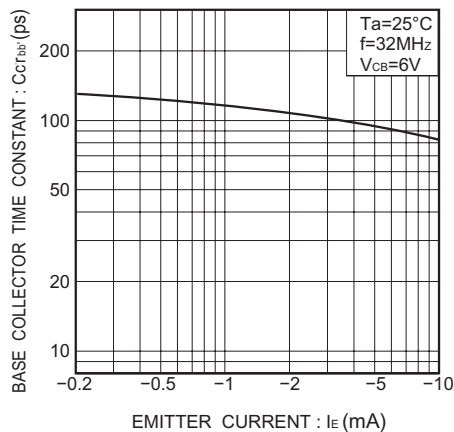
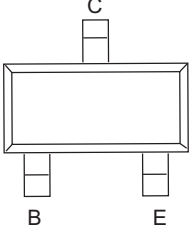
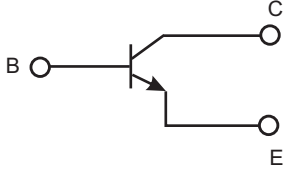


Fig.11 Base-collector time constant vs. emitter current



HSC2412K

Pinning information

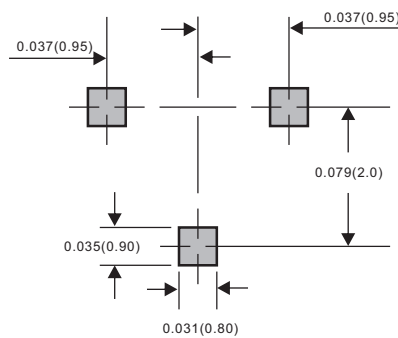
| Pin | Simplified outline | Symbol |
|---|---|---|
| PinB Base PinC Collector PinE Emitter |  |  |

Marking

| Type number | Marking code |
|-------------|--------------|
| HSC2412Q | BQ |
| HSC2412R | BR |
| HSC2412S | BS |

Suggested solder pad layout

SOT-23



Dimensions in inches and (millimeters)